 S/N 09/883795

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Leonard Forbes et al.	Examiner:	Theresa Doan
Serial No.:	09/883795	Group Art Unit:	2814
Filed:	June 18, 2001	Docket:	303.355US4
Title:	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE		

INFORMATION DISCLOSURE STATEMENT

Mail Stop RCE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement.

INFORMATION DISCLOSURE STATEMENT

Serial No :09 883795

Filing Date: June 18, 2001

Title: DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE

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Dkt: 303.355US4

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

LEONARD FORBES ET AL.

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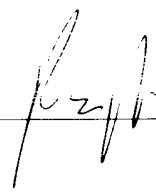
Date

29 AUGUST 2003

By

Robert E. Mates

Reg. No. 35,271

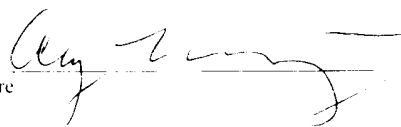


CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Mail Stop RCE, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 29th day of August, 2003.

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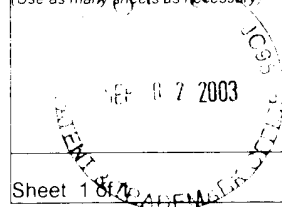


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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)



Complete if Known

Application Number	09/883795
Filing Date	June 18, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2814
Examiner Name	Doan, Theresa

Sheet 1 of 1

Attorney Docket No: 303.355US4

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		NEUDECK, P., et al., "Electrical Characterization of a JFET-Accessed GaAs Dynamic RAM Cell", <u>IEEE Electron Device Letters</u> , 10(11), (1989), pp. 477-480	
		QIAN, Q., et al., "Multi-Day Dynamic Storage of Holes at the AlAs/GaAs Interface" <u>IEEE Electron Device Letters</u> , EDL-7(11), (1986), pp. 607-609	
		RUSKA, W. S., "Microelectronic Processing", <u>McGraw-Hill Book Co.</u> , (1987), 281	
		SHARMA, B., et al., "Heterojunction Devices", In: <u>Semiconductor Heterojunctions</u> , Pergamon Press, New York, (1974), pp. 133-137	
		STREETMAN, B., In: <u>Solid State Electronic Devices</u> , 4th Edition, Prentice Hall, New Jersey, (1995), pp. 217-219, 392-394	

EXAMINER**DATE CONSIDERED**

Substitute Disclosure Statement Form (PTO 1449)

EXAMINER: Initial if reference considered; whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional). Applicant is to place a check mark here if English language Translation is attached.